L	Hits	Search Text	T	
Number			DB	Time stamp
1	51947	semiconductor and dram	<u> </u>	
		draw draw	USPAT;	2004/05/15
	*		US-PGPUB;	16:54
1	•		EPO; JPO;	
1	•		DERWENT;	
2	12799	/somi conduct and	IBM_TDB	
	12/33		USPAT;	2004/05/15
		recess\$2 or groove)	US-PGPUB;	16:54
ļ:			EPO; JPO;	
			DERWENT;	
3	877		IBM TDB	
	077	((semiconductor and dram) and (trench\$2	USPAT;	2004/05/15
1		Of fecess\$2 or groove)) and nitride and	US-PGPUB;	16:55
		liner "	EPO; JPO;	1 23.33
			DERWENT;	
1	100		IBM TDB	
7	197	(((semiconductor and dram) and (trench\$2	USPAT;	2004/05/15
٠.	ļ	or recess\$2 or groove)) and nitride and	US-PGPUB;	16:56
		liner) and collar and oxide	EPO; JPO;	10.30
			DERWENT;	
_	1		IBM TDB	
3 .	151	((((semiconductor and dram) and (trench\$2)	USPAT;	2004/05/15
		or recess\$2 or groove)) and nitride and	US-PGPUB;	2004/05/15
		liner) and collar and oxide) and gate		16:56
. ]			EPO; JPO;	
	<u> </u>		DERWENT;	
			IBM TDB	